

Supporting Information

for

Facile growth of a Sb_2Se_3 nanorods array induced by a MoSe_2 interlayer and its application to 3D p-n junction solar cells

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Figure S3. HADDF-STEM image of the $\text{Sb}_2\text{Se}_3/\text{MoSe}_2/\text{Mo}$ interface.

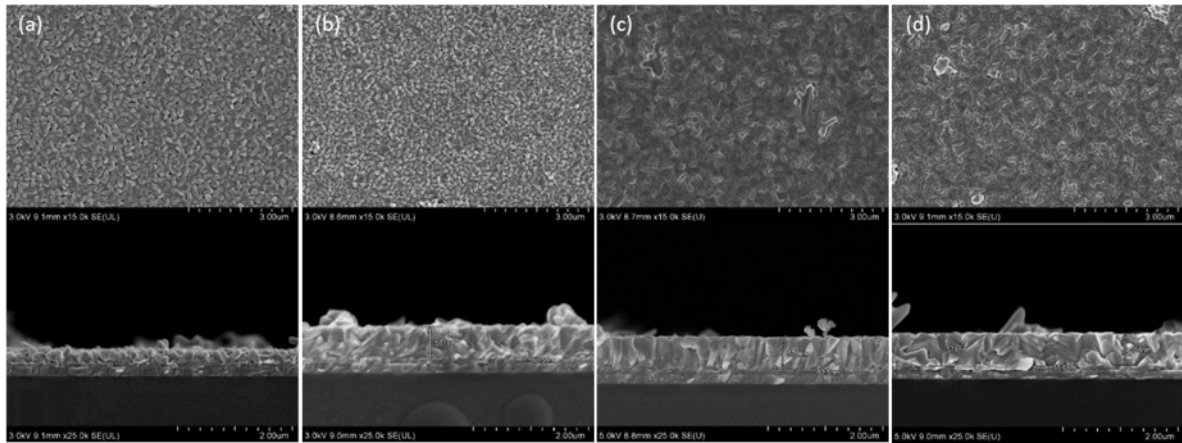


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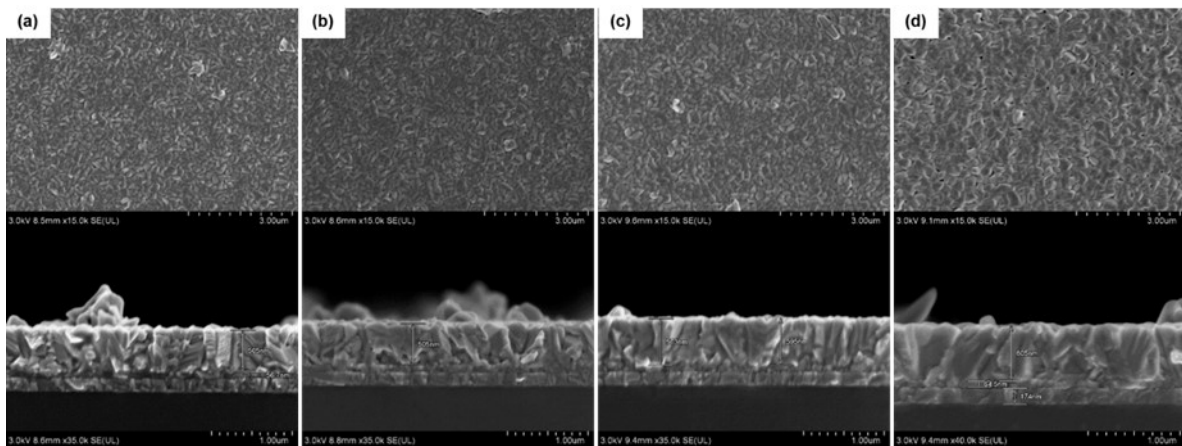


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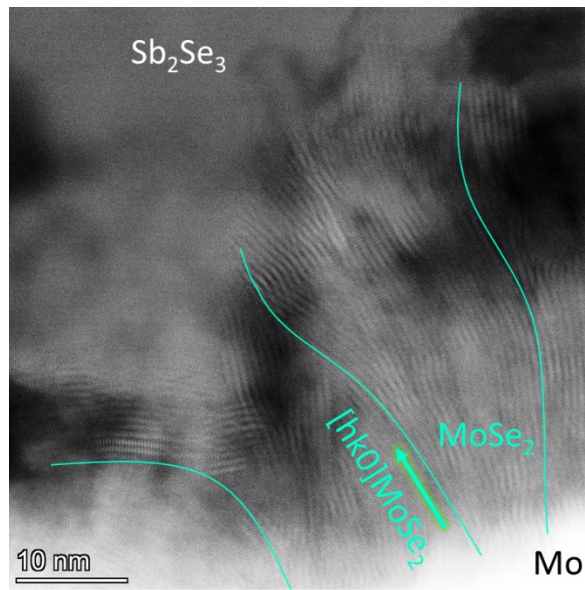


Figure S3: HADF-STEM image of the $\text{Sb}_2\text{Se}_3/\text{MoSe}_2/\text{Mo}$ interface.